

Silicon NPN Power Transistors

BU626A

DESCRIPTION

- With TO-3 package
- Short switching times.
- High dielectric strength.

APPLICATIONS

- For use in power supply units of TV receives.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

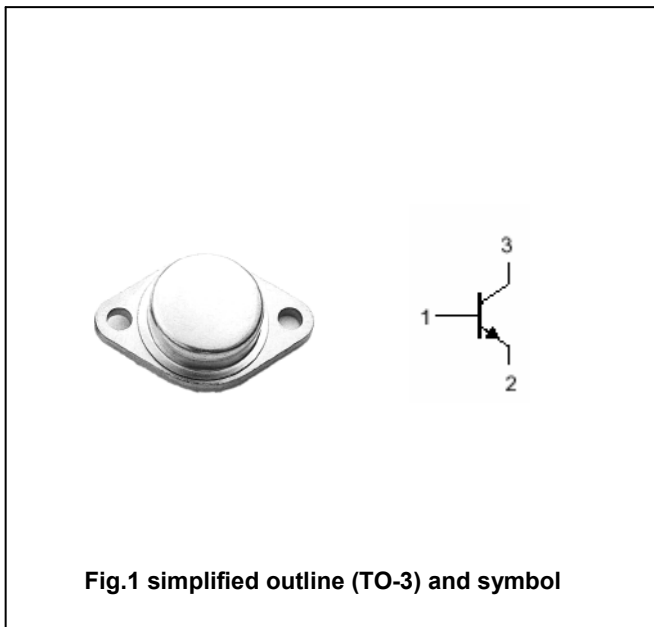


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1000	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		10	A
I _{CM}	Collector current-peak		15	A
P _T	Total power dissipation	T _C =25□	100	W
T _j	Junction temperature		175	□
T _{stg}	Storage temperature		-65~175	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-C}	Thermal resistance junction to case	1.5	K/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA; I _B =0;	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0;	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8A; I _B =2.5 A			3.3	V
V _{BEsat}	Base-emitter saturation voltage	I _C =8A; I _B =2.5 A			2.2	V
I _{CES}	Collector cut-off current	V _{CE} =1000V; V _{BE} =0			1.0	mA
h _{FE-1}	DC current gain	I _C =10A ; V _{CE} =1.5V	10			
h _{FE-2}	DC current gain	I _C =2.5A ; V _{CE} =10V	15			
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V		6		MHz
t _f	Fall time	I _C =8A; I _{B1} =-I _{B2} =2.5A;			1	μs

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PACKAGE OUTLINE

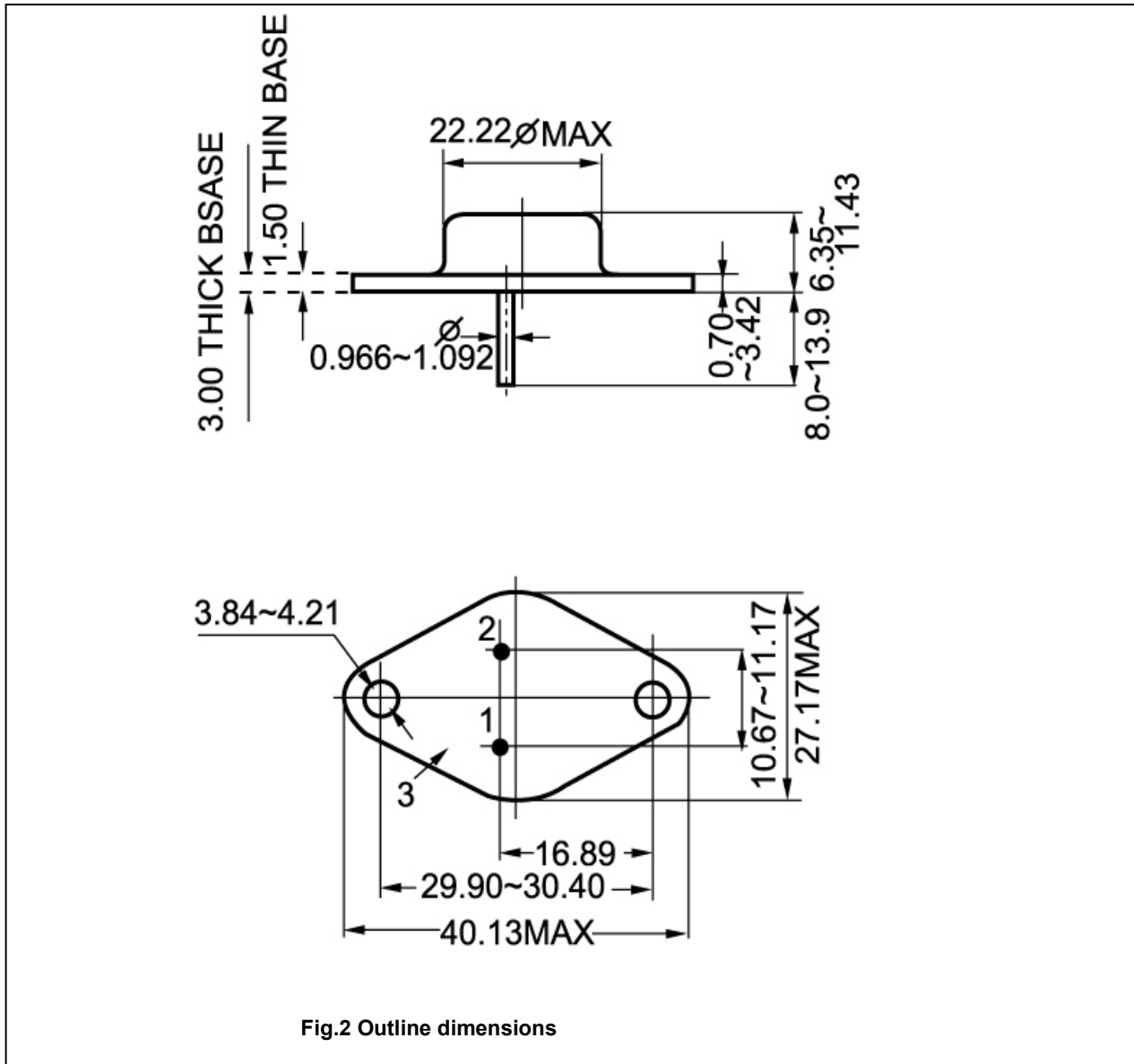


Fig.2 Outline dimensions